

2023 IEEE International Reliability Physics Symposium (IRPS 2023)

**Monterey, California, USA
26-30 March 2023**

Pages 1-525



**IEEE Catalog Number: CFP23RPS-POD
ISBN: 978-1-6654-5673-9**

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IEEE Catalog Number:	CFP23RPS-POD
ISBN (Print-On-Demand):	978-1-6654-5673-9
ISBN (Online):	978-1-6654-5672-2
ISSN:	1541-7026

Additional Copies of This Publication Are Available From:

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